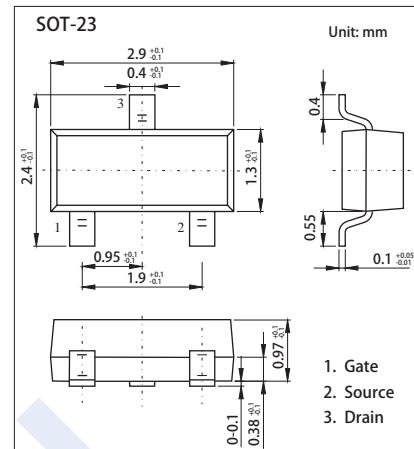
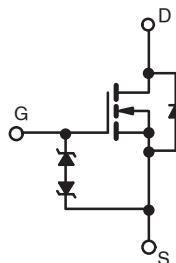


## N-Channel MOSFET

### BSS138 (KSS138)

#### ■ Features

- $V_{DS} (V) = 50V$
- $I_D = 300 \text{ mA } (V_{GS} = 10V)$
- $R_{DS(ON)} < 2.5 \Omega \text{ } (V_{GS} = 10V)$
- $R_{DS(ON)} < 3.5 \Omega \text{ } (V_{GS} = 4.5V)$
- Low On-Resistance
- ESD Rating: 1.5KV HBM



#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	50	V
Drain-Gate Voltage $R_{GS} \leq 20\text{ k}\Omega$	$V_{DG}$	50	
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	300	mA
Power Dissipation	$P_D$	300	mW
Thermal Resistance Junction-to-Ambient	$R_{thJA}$	417	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to 150	

#### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{DSS}$	$I_D=250 \mu\text{A}, V_{GS}=0\text{V}$	50			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=50\text{V}, V_{GS}=0\text{V}$			0.5	$\mu\text{A}$
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			$\pm 1$	$\mu\text{A}$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250 \mu\text{A}$	0.5		1.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=220\text{mA}$			2.5	$\Omega$
		$V_{GS}=4.5\text{V}, I_D=220\text{mA}$			3.5	
Forward Transconductance	$g_{FS}$	$V_{DS}=25\text{V}, I_D=0.3\text{A}, f=1\text{kHz}$	100			$\text{mS}$
Input Capacitance	$C_{iss}$	$V_{GS}=0\text{V}, V_{DS}=10\text{V}, f=1\text{MHz}$			50	$\text{pF}$
Output Capacitance	$C_{oss}$				25	
Reverse Transfer Capacitance	$C_{rss}$				8	
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=30\text{V}, I_D=0.3\text{A}, R_G=50 \Omega$			20	$\text{ns}$
Turn-Off Delay Time	$t_{d(off)}$				20	

#### ■ Marking

Marking	J1
---------	----

## N-Channel MOSFET

### BSS138 (KSS138)

#### ■ Typical Characteristics

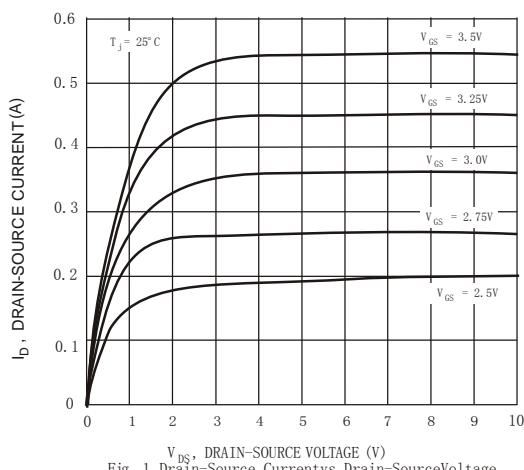


Fig. 1 Drain-Source Current vs. Drain-Source Voltage

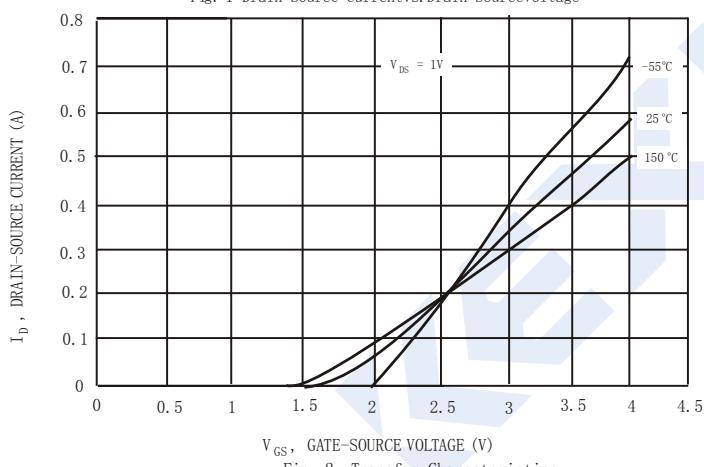


Fig. 2 Transfer Characteristics

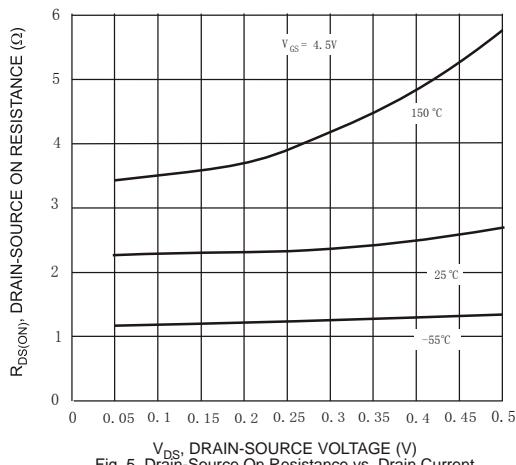


Fig. 5 Drain-Source On Resistance vs. Drain Current

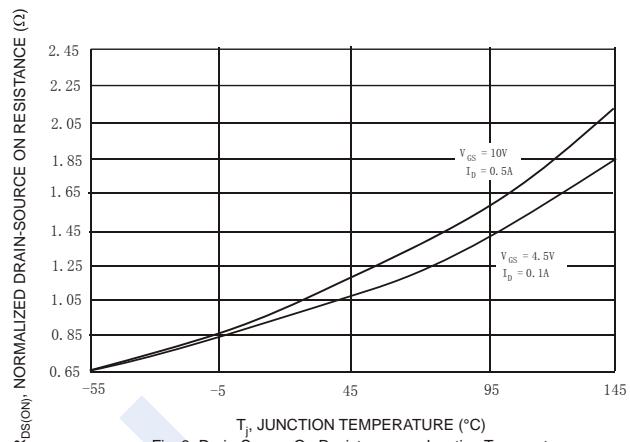


Fig. 3 Drain-Source On Resistance vs. Junction Temperature

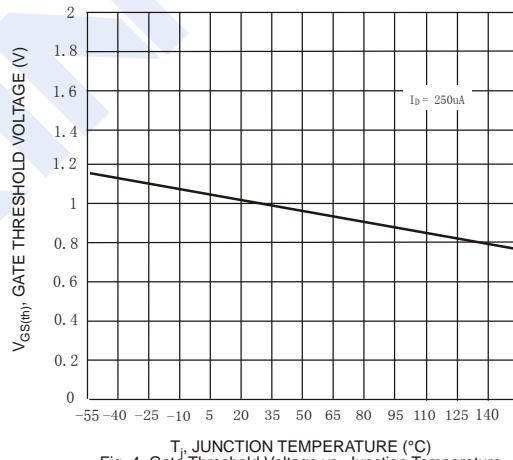


Fig. 4 Gate Threshold Voltage vs. Junction Temperature

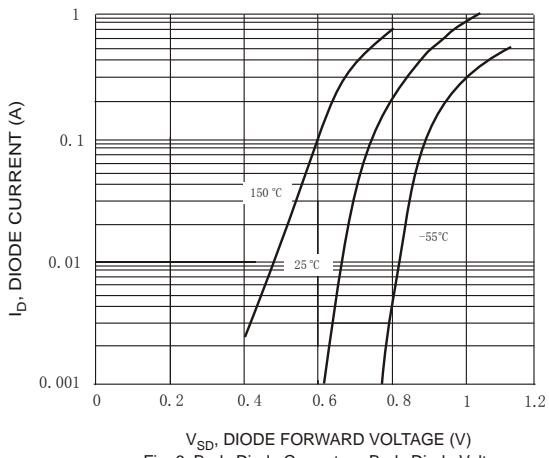


Fig. 6 Body Diode Current vs. Body Diode Voltage

## N-Channel MOSFET

### BSS138 (KSS138)

#### ■ Typical Characteristics

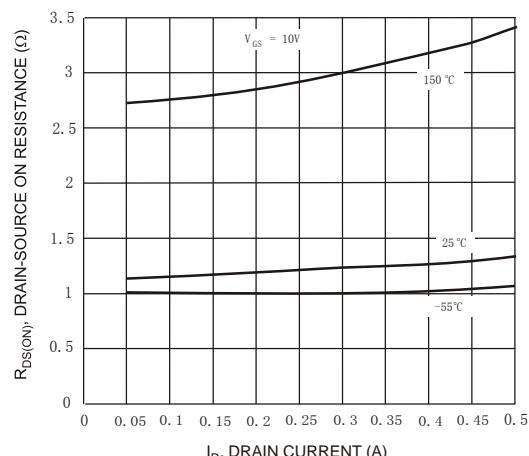


Fig. 7 Drain-Source On Resistance vs. Drain Current

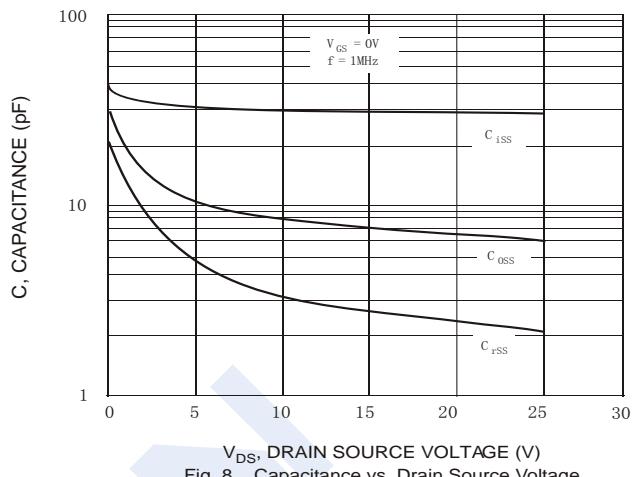


Fig. 8 Capacitance vs. Drain Source Voltage

# X-ON Electronics

Largest Supplier of Electrical and Electronic Components

***Click to view similar products for MOSFET category:***

***Click to view products by KEXIN manufacturer:***

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [FW216A-TL-2W](#) [FW231A-TL-E](#) [APT5010JVR](#) [NTNS3A92PZT5G](#)  
[IRF100S201](#) [JANTX2N5237](#) [2SK2464-TL-E](#) [2SK3818-DL-E](#) [FCA20N60\\_F109](#) [FDZ595PZ](#) [STD6600NT4G](#) [FSS804-TL-E](#) [2SJ277-DL-E](#)  
[2SK1691-DL-E](#) [2SK2545\(Q,T\)](#) [D2294UK](#) [405094E](#) [423220D](#) [MCH6646-TL-E](#) [TPCC8103,L1Q\(CM](#) [367-8430-0972-503](#) [VN1206L](#)  
[424134F](#) [026935X](#) [051075F](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [751625C](#) [873612G](#) [IRF7380TRHR](#)  
[IPS70R2K0CEAKMA1](#) [RJK60S3DPP-E0#T2](#) [RJK60S5DPK-M0#T0](#) [APT5010JVFR](#) [APT12031JFLL](#) [APT12040JVR](#) [DMN3404LQ-7](#)  
[NTE6400](#) [JANTX2N6796U](#) [JANTX2N6784U](#) [JANTXV2N5416U4](#) [SQM110N05-06L-GE3](#) [SIHF35N60E-GE3](#)